



安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

B5817WS-B5819WS-6AF

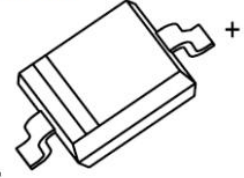
SOD-323 Schottky Barrier Rectifier Diode 肖特基势垒整流二极管



■Features 特点

Low forward voltage drop 低正向压降
High current capability 高电流能力
Surface mount device 表面贴装器件
Case 封装:SOD-323

SOD-323



■Maximum Rating 最大额定值

(T_A=25°C unless otherWise noted 如无特殊说明, 温度为 25°C)

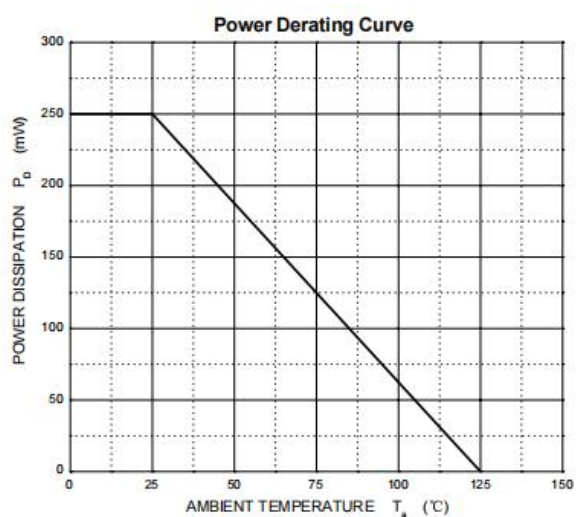
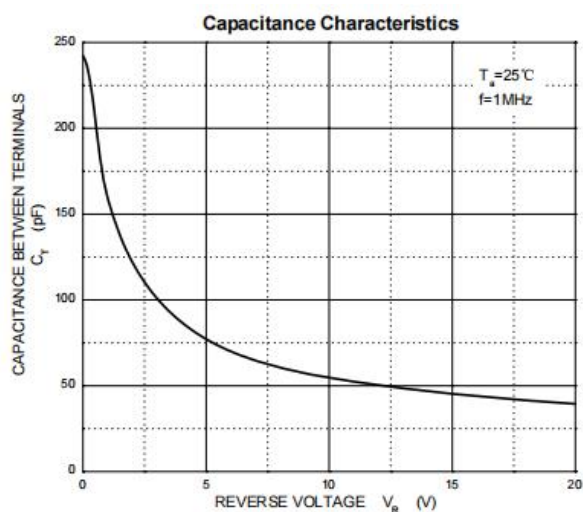
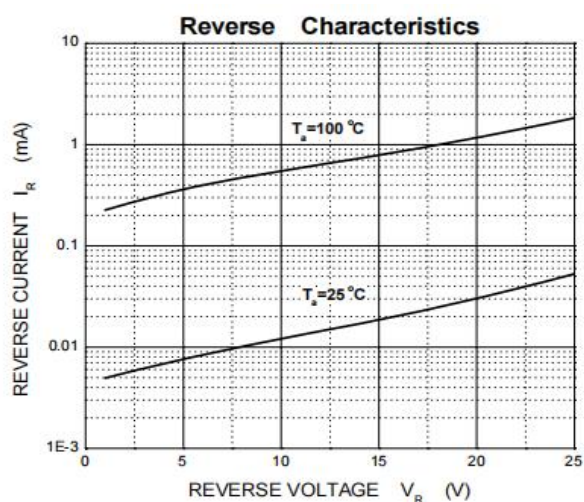
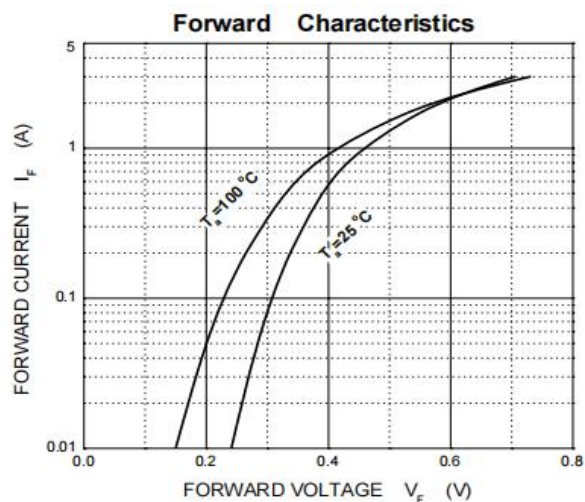
Characteristic 特性参数	Symbol 符号	B5817WS -6AF	B5818WS -6AF	B5819WS -6AF	Unit 单位
Device Marking 产品印字		SJ	SK	SL	
Peak Reverse Voltage 反向峰值电压	V _{RRM}	20	30	40	V
DC Reverse Voltage 直流反向电压	V _R	20	30	40	V
RMS Reverse Voltage 反向电压均方根值	V _{R(RMS)}	14	21	28	V
ForWSard Rectified Current 正向整流电流	I _F	1			A
Peak Surge Current 峰值浪涌电流	I _{FSM}	9			A
Repetitive Peak Surge Current 重复峰值浪涌电流	I _{FRM}	1.5			A
PoWSeR Dissipation 耗散功率	P _D	250			mW
Thermal Resistance J-A 结到环境热阻	R _{θJA}	500			°C/W
Junction/Storage Temperature 结温/储藏温度	T _J , T _{stg}	-50to+150°C			°C

■Electrical Characteristics 电特性

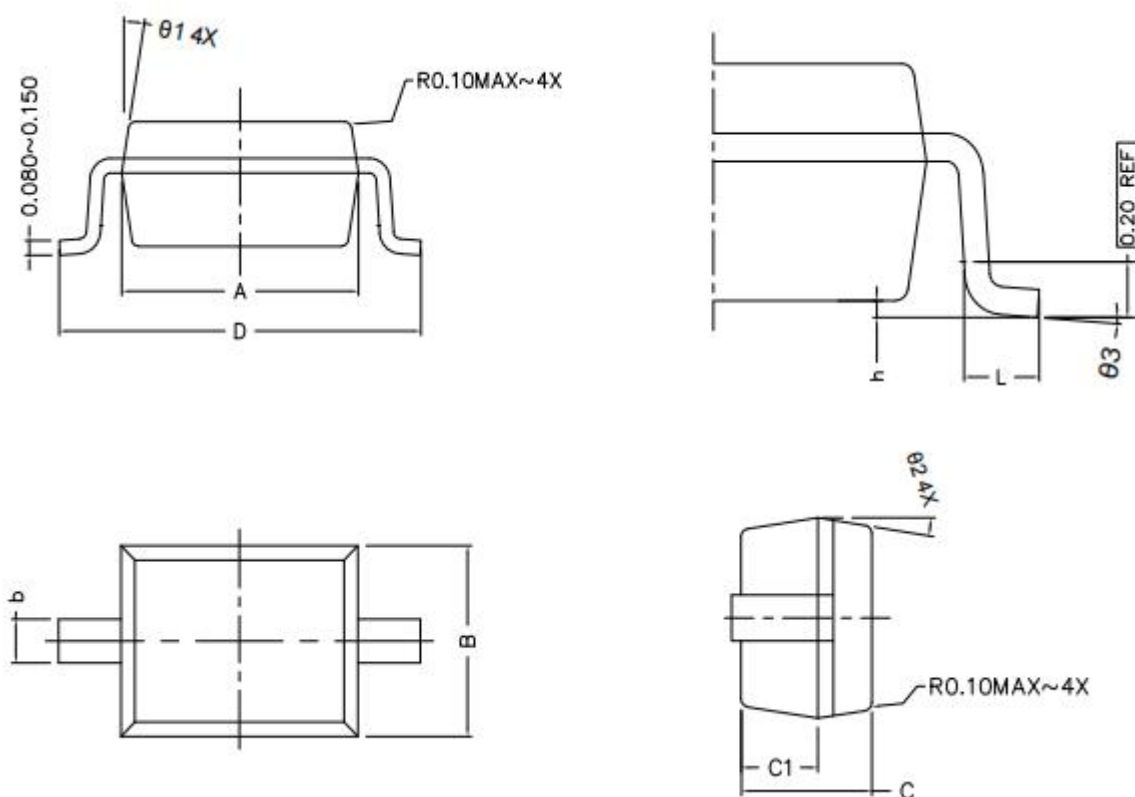
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Characteristic 特性参数	Symbol 符号	B5817WS -6AF	B5818WS -6AF	B5819WS -6AF	Unit 单位	Condition 条件
Reverse Voltage 反向电压	V _R	20	30	40	V	I _R =1mA
ForWSard Voltage 正向电压	V _F	0.45 0.75	0.55 0.875	0.6 0.9	V	I _F =1A I _F =3A
Reverse Current 反向电流	I _R	0.05@T _a =25°C 8@T _a =100°C			mA	V _R =V _{RRM}
Diode Capacitance 二极管电容	C _T	120			pF	V _R =4V,f=1MHz

■ Typical Characteristic Curve 典型特性曲线



■ Dimension 外形封装尺寸 SOD-323



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.600	1.800	0.063	0.071
B	1.200	1.400	0.047	0.055
C	0.750	0.950	0.030	0.037
C1	0.450	0.550	0.018	0.022
D	2.450	2.800	0.096	0.110
L	0.200	0.400	0.008	0.016
b	0.200	0.400	0.008	0.016
h	0.020	0.120	0.001	0.005
$\ominus 3$	0°	8°	0°	8°